

SuperMOS – SOT-23 -20V V_{DSS} , 36m Ω $R_{DS(on)}$, P-channel MOSFET

1. Description

The ESPM2341-3/TR is P-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product ESPM2341-3/TR is Pb-free.

2. Features

- -20V, $R_{DS(ON)}=36m\Omega(TYP.) @V_{GS}=-4.5V$
- $R_{DS(ON)}=50m\Omega(TYP.) @V_{GS}=-2.5V$
- $R_{DS(ON)}=72m\Omega(TYP.) @V_{GS}=-1.8V$
- Fast Switching
- High density cell design for low $R_{DS(on)}$
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

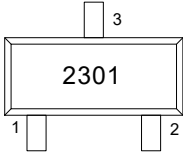
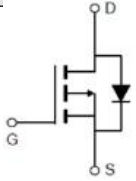
3. Applications

- PWM applications
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

4. Ordering Information

Part Number	Package	Marking	Material	Packing	Quantity per reel	Flammability Rating	Reel Size
ESPM2341-3/TR	SOT-23	2301	Halogen free	Tape & Reel	3,000 PCS	UL 94V-0	7 inches

5. Pin Configuration and Functions

Pin	Function	Outline	Circuit Diagram
1	Gate		
2	Source		
3	Drain		

6. Specification

Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	BV_{DSS}	-20	V	
Gate-Source Voltage	V_{GS}	± 12	V	
Continuous Drain Current	I_D	$T_A=25^\circ\text{C}$	-3.3	A
		$T_A=100^\circ\text{C}$	-2.1	
Maximum Power Dissipation	P_D	0.9	W	
Pulsed Drain Current	I_{DM}	-13.4	A	
Operating Junction Temperature	T_J	150	$^\circ\text{C}$	
Storage Temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$	

Thermal resistance ratings

Single Operation				
Parameter	Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance ($t \leq 10\text{s}$)	$R_{\theta JA}$		139	$^\circ\text{C}/\text{W}$

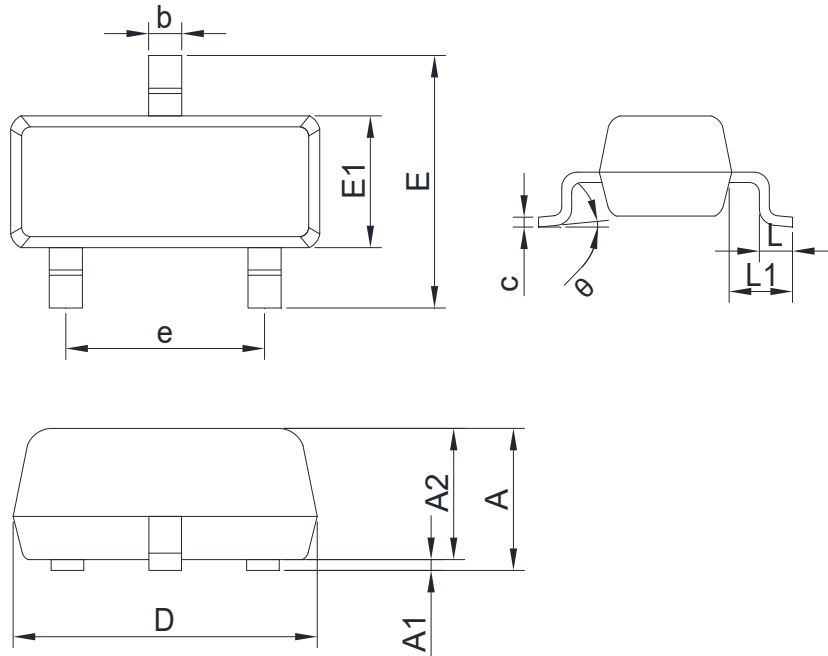
Electrical Characteristics

At TA = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-20V, V_{GS}=0V$			-1	μA
Gate-to-source Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 12V$			± 100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=-250\mu A$	-0.4	-0.62	-1.0	V
Drain-to-source On-resistance	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=-2A$		36	47	m Ω
		$V_{GS}=-2.5V, I_D=-1.5A$		50	63	
		$V_{GS}=-1.8V, I_D=-1A$		72	90	
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C_{ISS}	$V_{GS}=0V, V_{DS}=-10V$ $f=1MHz$		430		pF
Output Capacitance	C_{OSS}			65		
Reverse Transfer Capacitance	C_{RSS}			52		
Total Gate Charge	Q_G	$V_{GS}=-4.5V, V_{DS}=-10V$ $I_D=-2A$		4.3		nC
Gate-to-Source Charge	Q_{GS}			0.8		
Gate-to-Drain Charge	Q_{GD}			1.1		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS}=-4.5V, V_{DS}=-10V$ $I_D=-2A, R_G=3\Omega$		12		ns
Rise Time	t_r			55		
Turn-Off Delay Time	$t_{d(OFF)}$			15		
Fall Time	t_f			9		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=-2A$			-1.5	V

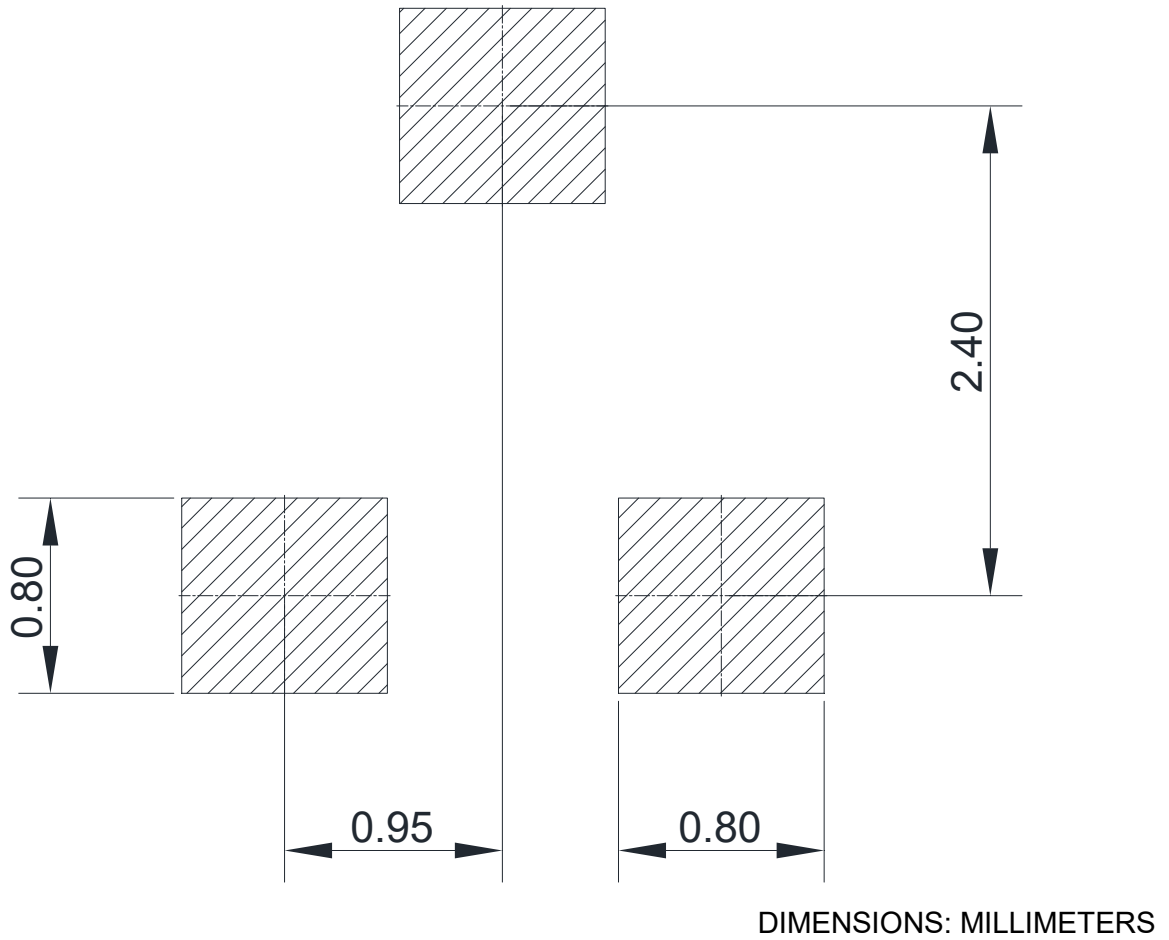
7. Dimension (SOT-23)

POD(Z)



COMMON DIMENSIONS CUNITS MEASURE=MILLIMETER					
SYMBOL	MIN	MAX	SYMBOL	MIN	MAX
A	0.90	1.20	E	2.25	2.55
A1	0.00	0.10	E1	1.20	1.40
A2	0.90	1.10	e	1.80	2.00
b	0.30	0.50	L	0.30	0.50
c	0.07	0.18	L1	0.475	0.625
D	2.80	3.04	θ	0°	8°

8. Recommended Soldering Footprint



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